

1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



PHE13003A

NPN power transistor Rev. 02 — 29 July 2010

Product data sheet

Product profile 1.

1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) 3 leads plastic package.

1.2 Features and benefits

Fast switching

■ High voltage capability of 700 V

1.3 Applications

- Compact fluorescent lamps (CFL)
- Electronic lighting ballasts
- Inverters
- Off-line self-oscillating power supplies

1.4 Quick reference data

Table 1. Quick reference data

$\begin{array}{cccccccccccccccccccccccccccccccccccc$	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\begin{tabular}{l lllllllllllllllllllllllllllllllllll$	I_{C}	collector current	DC; see Figure 2	-	-	1	Α
$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	P _{tot}	•	T _{lead} ≤ 25 °C; see <u>Figure 1</u>	-	-	2.1	W
h _{FE} DC current gain $I_C = 0.8 \text{ A}; V_{CE} = 5 \text{ V};$ 5 7.5 20 $T_{lead} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{\text{Figure 8}};$	V _{CESM}		$V_{BE} = 0 V$	-	-	700	V
T _{lead} = 25 °C; see <u>Figure 8</u> ;	Static chara	acteristics					
See <u>rigure 9</u>	h _{FE}	DC current gain		5	7.5	20	



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	С	collector		C I
3	E	emitter		BE sym123
			SOT54 (TO-92)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHE13003A	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	700	V
V _{CBO}	collector-base voltage	I _E = 0 A	-	700	V
V _{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
I _C	collector current	DC; see Figure 2	-	1	Α
I _{CM}	peak collector current		-	2	Α
I _B	base current	DC	-	0.5	Α
I _{BM}	peak base current		-	1	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; see <u>Figure 1</u>	-	2.1	W
T _{stg}	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C
V _{EBO}	emitter-base voltage	I _C = 0 A; I(Emitter) = 10 mA	-	9	V

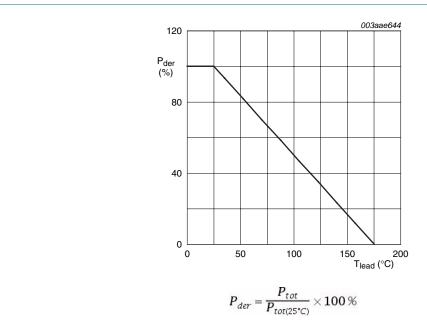
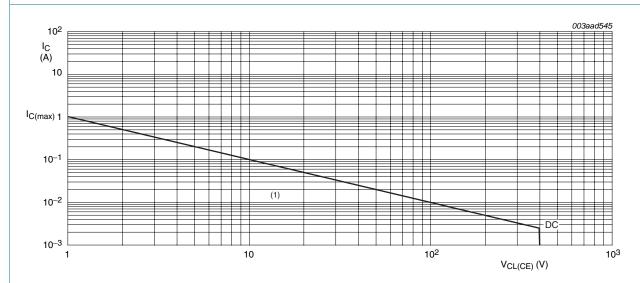


Fig 1. Normalized total power dissipation as a function of lead temperature



 $T_{lead} \le 25$ °C(1)Region of permissible DC operation

Fig 2. Forward bias safe operating area

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	see Figure 3	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed-circuit board mounted; lead length = 4 mm	-	150	-	K/W

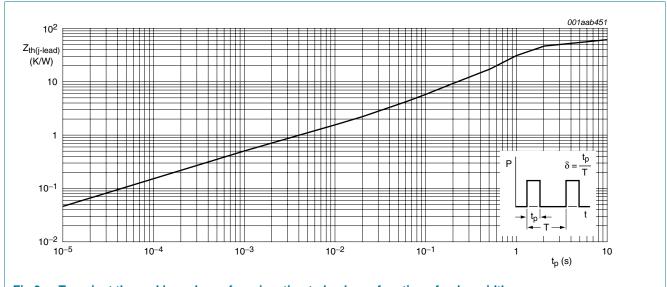
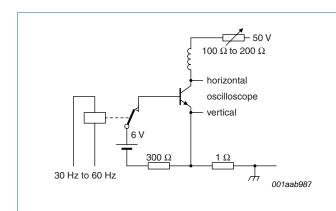


Fig 3. Transient thermal impedance from junction to lead as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
I _{CES}	collector-emitter cut-off current	$V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 125 \text{ °C}$	-	-	5	mA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	-	1	mA
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0 \text{ A}$; $I_C = 1 \text{ mA}$; $L_C = 25 \text{ mH}$; $T_{lead} = 25 ^{\circ}\text{C}$; see Figure 4; see Figure 5	400	-	-	V
V _{CEsat}	collector-emitter saturation voltage	I_C = 0.25 A; I_B = 50 mA; T_{lead} = 25 °C; see Figure 6	-	0.2	0.5	V
		I_C = 0.5 A; I_B = 125 mA; T_{lead} = 25 °C; see Figure 6	-	0.3	1	V
		I_C = 0.75 A; I_B = 250 mA; T_{lead} = 25 °C; see Figure 6	-	0.4	1.5	V
V _{BEsat}	base-emitter saturation voltage	I_C = 0.25 A; I_B = 50 mA; T_{lead} = 25 °C; see Figure 7	-	-	1	V
		I_C = 0.5 A; I_B = 125 mA; T_{lead} = 25 °C; see Figure 7	-	-	1.2	V
h _{FE}	DC current gain	I_C = 0.5 mA; V_{CE} = 2 V; T_{lead} = 25 °C; see <u>Figure 8</u> ; see <u>Figure 9</u>	12	-	-	
		I _C = 0.4 A; V _{CE} = 5 V; T _{lead} = 25 °C; see <u>Figure 8</u> ; see <u>Figure 9</u>	10	-	30	
		I _C = 0.8 A; V _{CE} = 5 V; T _{lead} = 25 °C; see <u>Figure 8</u> ; see <u>Figure 9</u>	5	7.5	20	
Dynamic ch	aracteristics					
t _f	fall time	I_C = 1 A; I_{Bon} = 200 mA; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; see Figure 10; see Figure 11	-	80	-	ns





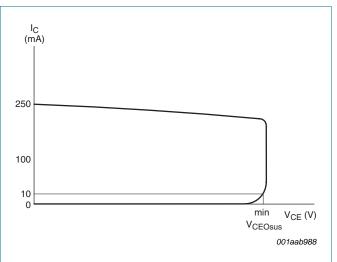


Fig 5. Oscilloscope display for collector-emitter sustaining voltage test waveform

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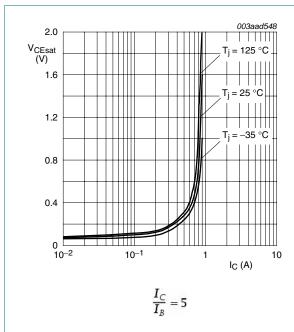


Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values

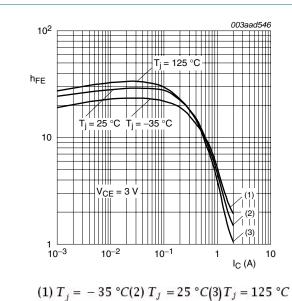


Fig 8. DC current gain as a function of collector current; typical values

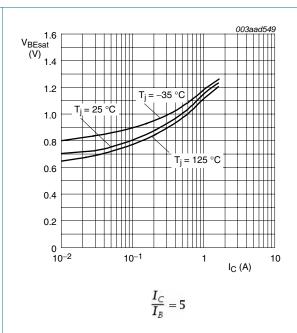
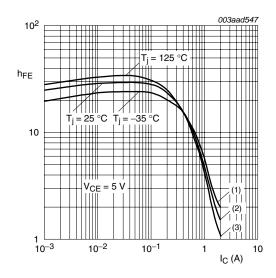


Fig 7. Base-emitter saturation voltage as a function of collector current; typical values



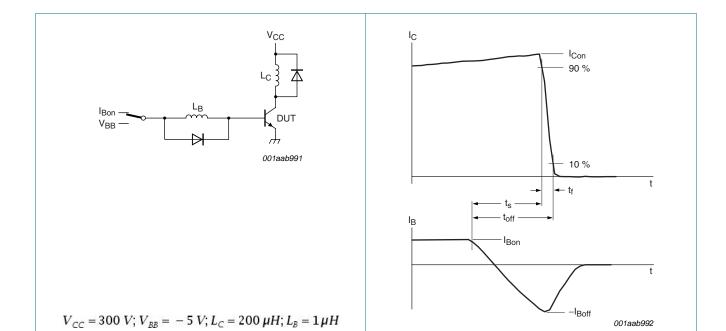
(1) $T_j = -35 \,^{\circ}C(2) \, T_j = 25 \,^{\circ}C(3) \, T_j = 125 \,^{\circ}C$

Fig 9. DC current gain as a function of collector current; typical values

Fig 10. Test circuit for inductive load switching

Fig 11. Switching times waveforms for inductive load

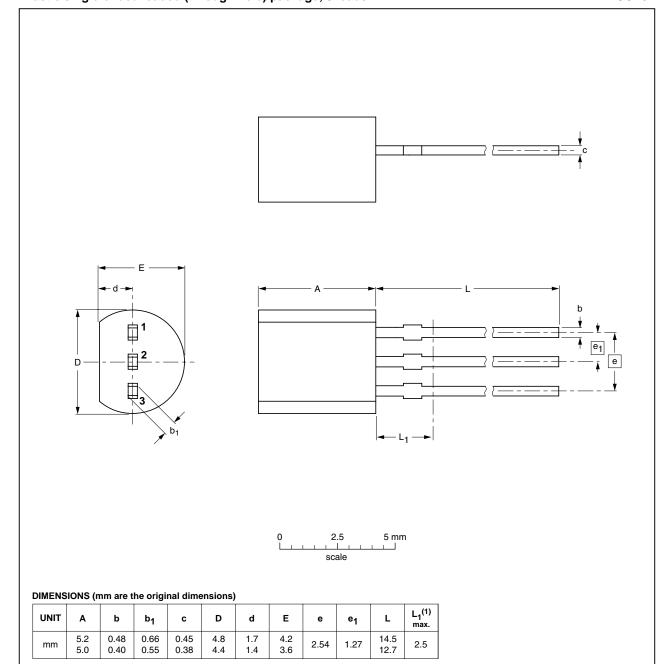
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7. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFERENCES			EUROPEAN ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			-04-06-28 04-11-16

Fig 12. Package outline SOT54 (TO-92)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHE13003A v.2	20100729	Product data sheet	-	PHE13003A v.1
Modifications:	 Various chang 	ges to content.		
PHE13003A v.1	20090813	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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